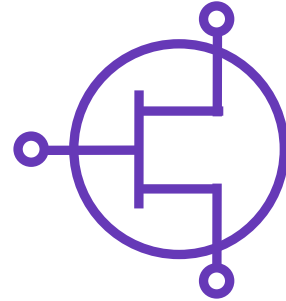


## Model Features

- Broadband (DC to 40 GHz)
- Large-signal model (Modelithics-Enhanced Angelov)
- Measurement Validations:
  - Pulsed I-V (25 C to 85 C)
  - Multi-bias S-parameters (25 C to 85 C)
  - Load pull (25 C), 12 and 18 GHz
  - IP3 linearity validation, 12 GHz, 7 V 60%*I*<sub>DSS</sub>
- Advanced model feature: enabling intrinsic I-V sensing.



**MES-MWT-MWT9F-001**  
**MwT-9F**  
**Discrete GaAs MESFET**

## Model Description

The MES-MWT-MWT9F-001 is a non-linear model for the MwT-9F a discrete 750 um GaAs MESFET (additional information is available at [www.mwtinc.com](http://www.mwtinc.com)). The model is based on the extraction of a customized Angelov non-linear model that is validated against the following Modelithics measurement data: I-V, S-parameters, load pull and IP3.

## Technical Notes

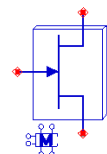
Model is optimized for 2, 4 and 7 V operation (65 mA (30% *I*<sub>DSS</sub>), 109 mA (50% *I*<sub>DSS</sub>) and 131 mA (60% *I*<sub>DSS</sub>)).

- Model Parameters:
  - **VDSQ**: For setting the optimum bias point of the model (default=7 V).
  - **Temperature**: represents the backside ambient temperature, validated at 25 C and 85 C.
  - **Self\_heat**: switch for the electrothermal model (0 or 1), 0= self-heating is turned off, 1 (default)= self-heating is turned on.
  - **BWremoval**: 0 includes wire assembly (only used in measurements, 1 (default) sets model reference planes at the center of the gate, drain, and source bond pads.
  - [Modelithics Micro Probe Accessories](#) part number 0503, 5 mil Alumina adapter substrates were used to access the bond pads of discrete die.

## Model Simulation Settings

- **I-V**: self\_heat: 0 for I-V simulations (self heating model turned OFF), Temperature=25 C
- **S-Parameters**: self\_heat: 1 for CW bias, Temperature=25 C
- **Load Pull Single-tone and two tone validations**: self\_heat: 1 for CW bias; Temperature=25 C.

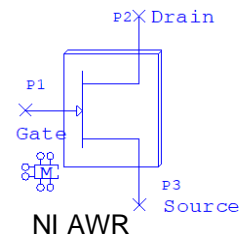
## Model Representation



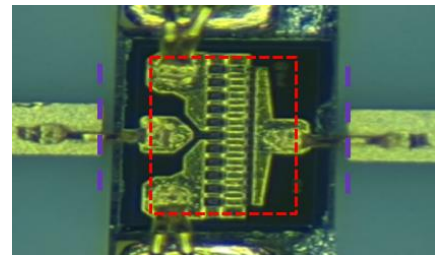
MES\_MWT\_MWT9F\_001\_Final  
 X48  
 VDQ=7 V  
 Temperature=25  
 self\_heating=1  
 BWremoval=0

Keysight ADS

SUBCKT  
 ID=S4  
 NET="MES\_MWT\_MWT9F\_001"  
 Temperature=25 DegC  
 VDQ=7 V  
 self\_heating=1  
 BWremoval=0



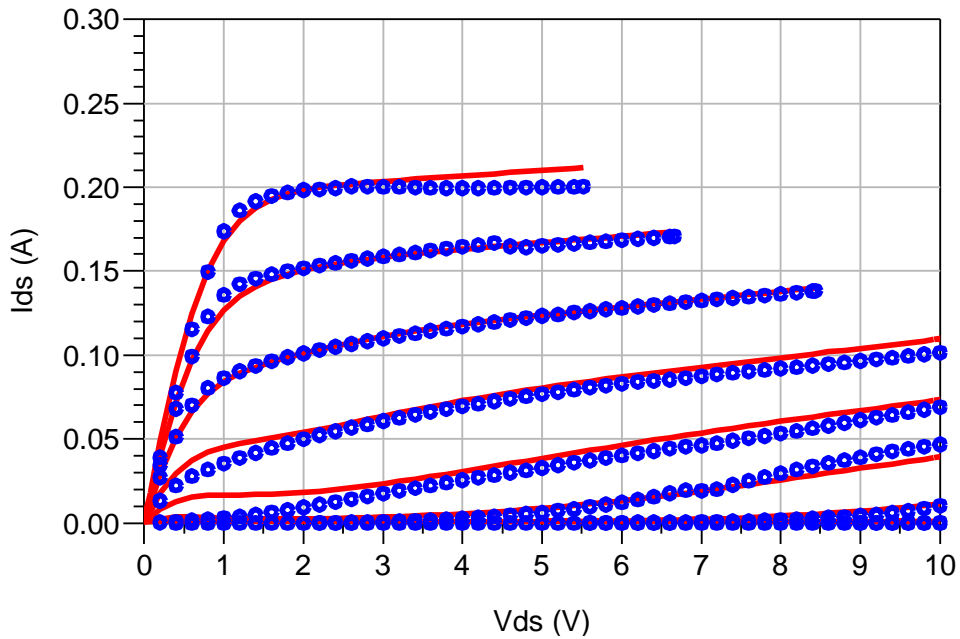
## Reference Planes



Model and Measurement Reference Planes (BWremoval=1)

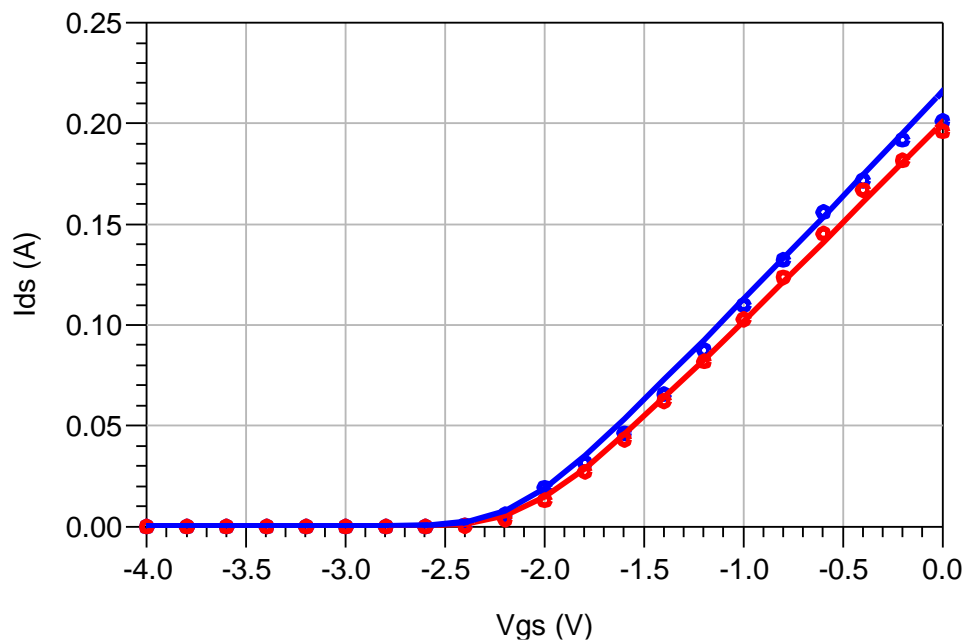
Model and Measurement Reference Planes (BWremoval=0)

DC I-V Characteristics: VDSQ = 7 V, 25 C



Legend: Red Solid lines - Model data, O Symbols - Measured data  
 Simulated at 25 C with VGS varying from -4 to 0 V in steps of 0.4 V,  
 VDS varying from 0 to 10 V in steps of 0.25 V. Model self\_heat = 0.

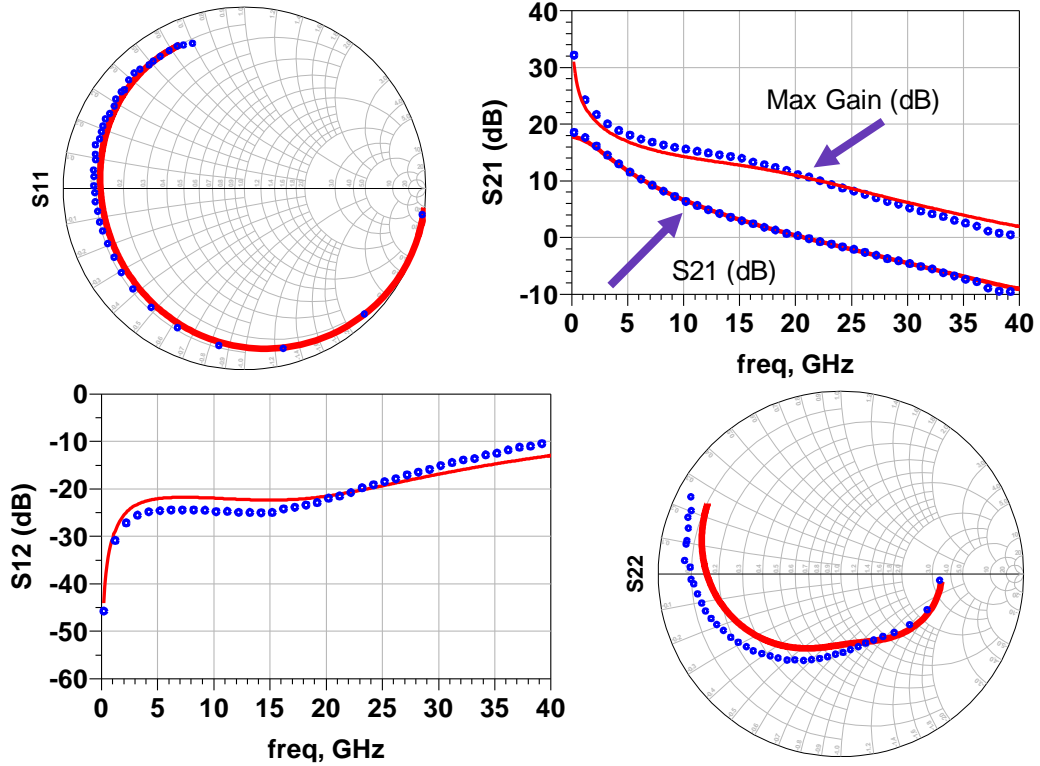
Model vs. Measurement Temperature IV Characteristics



Legend: Red Solid lines: 85 C, Blue Solid lines: 25 C.  
 Solid lines - Model data, Symbols - Measured data  
 Simulated at 25 C and 85 C, VDSQ of 7 V. Model self\_heat = 0.

S-Parameters Model vs. Measured:

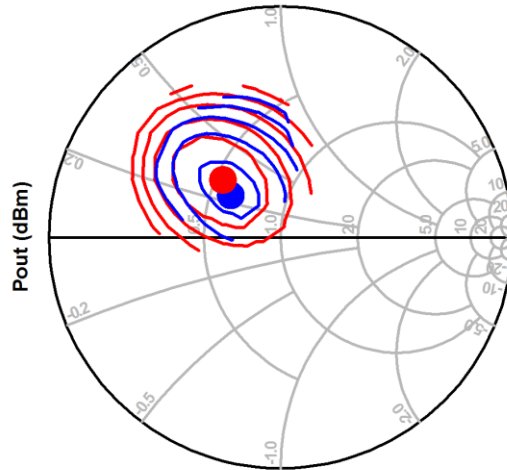
VDS = 7 V, VGS = -0.79 V, IDS = 130.5 mA (60% IDSS), 25 C



Legend: Red Solid lines - Model data, O Symbols - Measured data  
 Simulated at 25 C with the frequency range from 0.2 – 40 GHz. 50 Ω Smith Charts  
 BWremoval = 0

Load Pull Validation: Frequency = 12 GHz  
 VDS = 7 V, VGS = -0.79 V, IDS = 130.5 mA (60% IDSS),  
 Input Power = 18 dBm, Z0 = 50 Ω Center, 25 C

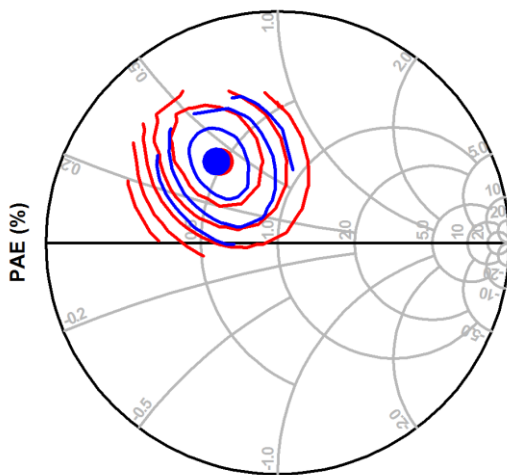
Power Tuning (0.5 dB contour step)



Test Bench Impedances  
 (Ohms):

ZS = 8.2 + j\*5.5  
 ZS2 = 77.0 + j\*26.4  
 ZS3 = 41.3 + j\*23.8  
 ZLoad2 = 73.6 - j\*16.3  
 ZLoad3 = 81.4 - j\*47.1

Efficiency Tuning (5% contour step)



Legend: Red Solid lines – Model, Blue Solid lines – Measured, BWremoval = 0

Load Pull Summary	Max Power Load Impedance (Ohms)	Max Power Value (dBm)	Max PAE Load Impedance (Ohms)	Max PAE Value (%)
Measured	30.4 + j*12.0	27.2	23.3 + j*20.3	47.7
Model	28.3 + j*17.1	27.1	17.9 + j*20.1	51.1

Load pull data has been processed for contour display.

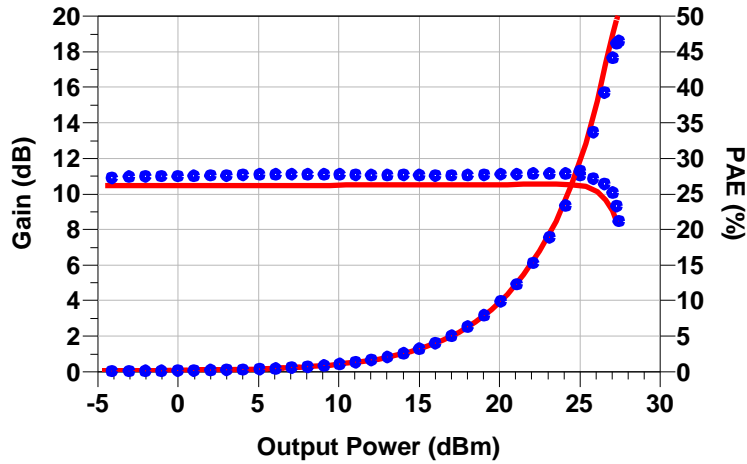
Single Tone Power Sweep: Frequency = 12 GHz  
 VDS = 7 V, VGS = -0.79 V, IDS = 130.5 mA (60% IDSS), 25 C

Load Condition: Measured Power Tuned

Transducer Gain and Power Added Efficiency (PAE)

Load Condition: Power Tuned  
 Test Bench Impedances  
 (Ohms):

- ZS = 8.2 + j\*5.5
- ZS2 = 77.0 + j\*26.4
- ZS3 = 41.3 + j\*23.8
- ZLoad = 30.4 + j\*12.0
- ZLoad2 = 82.3 - j\*4.8
- ZLoad3 = 81.4 - j\*47.1



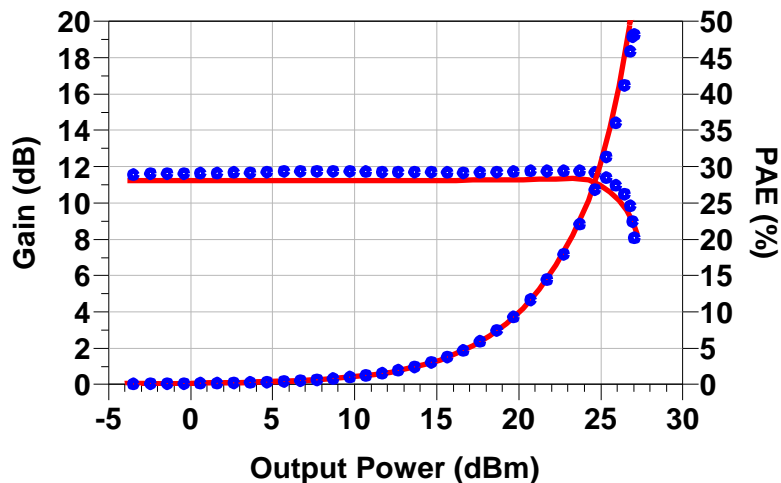
Legend: Red Solid lines - Model data, O Symbols - Measured data, BWremoval = 0

Load Condition: Measured PAE Tuned

Transducer Gain and Power Added Efficiency (PAE)

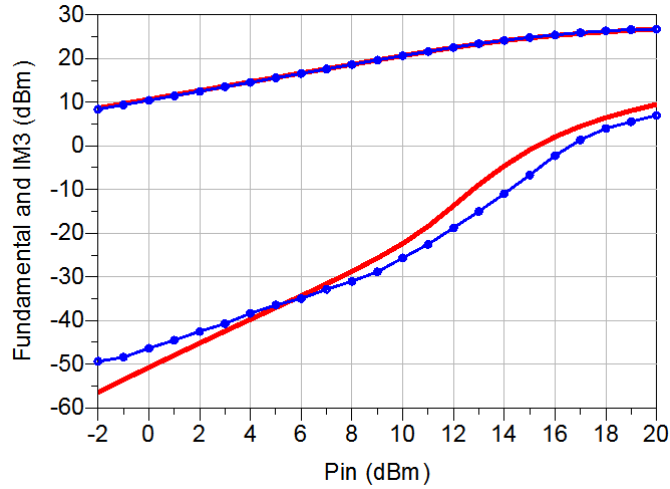
Load Condition: PAE Tuned  
 Test Bench Impedances  
 (Ohms):

- ZS = 8.2 + j\*5.5
- ZS2 = 84.9 + j\*30.0
- ZS3 = 41.3 + j\*23.8
- ZLoad = 23.3 + j\*20.3
- ZLoad2 = 90.3 - j\*13.3
- ZLoad3 = 81.4 - j\*47.1

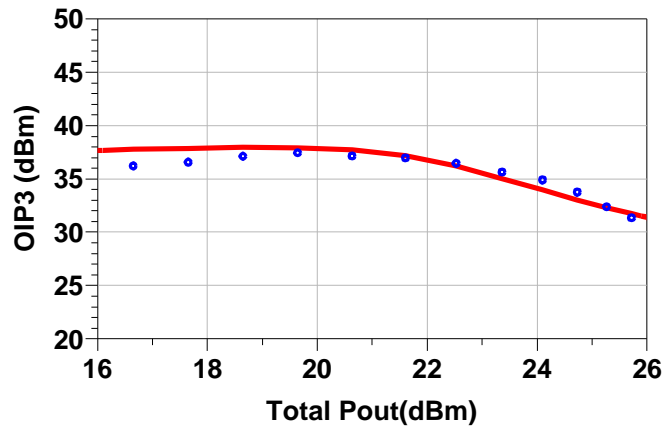


Legend: Red Solid lines - Model data, O Symbols - Measured data, BWremoval = 0

### Two Tone Validation 12 GHz



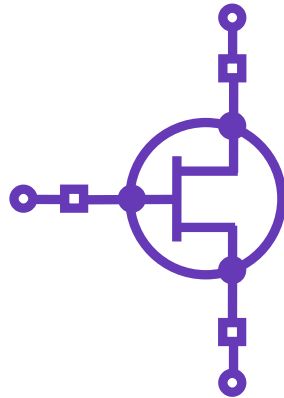
Simulated (solid line) and measured (symbols) tuned for max Power.  
 Source impedance =  $(7 + j*3.6)$  ohms, load impedance =  $(29 + j*12.3)$  Ohms.  
 Frequency = 12 GHz, 5 MHz tone spacing, Vds = 7 V, 130 mA (60%Idss)



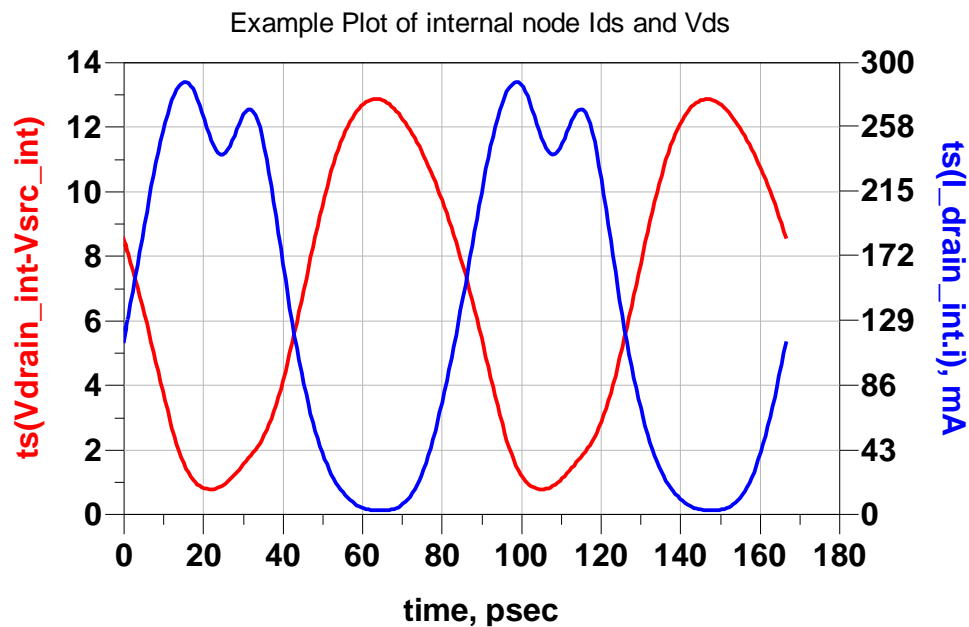
Simulated (solid line) and measured (symbols) tuned for max Power.  
 Source impedance =  $(7 + j*3.6)$  Ohms, load impedance =  $(29 + j*12.3)$  Ohms.  
 Frequency = 12 GHz, 5 MHz tone spacing, Vds = 7 V, 130 mA (60%Idss)

## Advanced Model Features: Intrinsic Voltage/Current Sensing

Get Vds and Ids model data near current generator intrinsic planes while tuning.

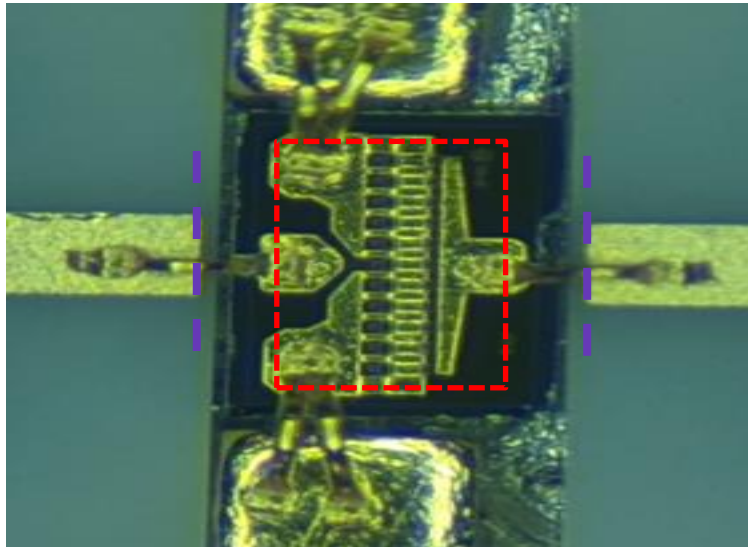


- External Model Planes
- Internal Model Planes for I/V waveform analysis
- Parasitic networks available separately from intrinsic I/V model



Results based on harmonic balance simulation at 17 dBm input power, PAE matched at 12 GHz, 7 V, and 131 mA.  $ZS = (8.2 + j*5.5)$  Ohms,  $ZS2 = (77.0 + j*26.4)$  Ohms,  $ZS3 = (41.3 + j*23.8)$  Ohms,  $ZLoad = (30.4 + j*12.0)$  Ohms,  $ZLoad2 = (82.3 - j*4.8)$  Ohms,  $ZLoad3 = (81.4 - j*47.1)$  Ohms

## Assembly Diagram



Test fixture details:

[Modelithics Micro Probe Accessories](#) part number 0503, 5 mil Alumina adapter substrates were used to access the bond pads of discrete die.

- Device thickness: 3.93 mil
- Test board thickness: 5 mil
- Bond-wire diameter: 1 mil gold
- Gate and Drain single bond-wire length: 6 mil +/-2 (average)
- Source bond-wire length (two wires per source pad): 6 mil +/-2 (average)
- Metal standoff external next to each source pad is 4 mil thick, its purpose is to shorten the bondwire lengths to the source/ground.
- Blue line is model planes with bondwires ON (BWremoval=0)
- Red line is model planes with bondwires OFF (BWremoval=1)

## Model and Datasheet Revision Notes

03/07/2023	Original model and datasheet development
06/21/2023	Datasheet updated with IP3 validation